INFORMATION DISCLOSURE CITATION

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09/936,560

APPLICANT

WALLIS et al

(Use several sheets if necessary)

GROUP

14 September 2001

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	A. Mazuelas et al, "Strain compensation in highly carbon doped GaAs/AlAs distributed Bragg reflectors"
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Examiner: Initial if reference considered, whether or not citation is of conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

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